## IN THE CLAIMS:

Please revise the claims to read as follows.

1. (Currently amended) A group III nitride compound semiconductor light-emitting device, comprising:

a light-emitting layer of a multilayer quantum well structure comprising alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer,

wherein said n-type clad layer is made thicker than each of said barrier layers and the thickness of said n-type clad layer is in a range of 100 Å to 500 Å, and

wherein said n-type clad layer is formed of a material substantially the same as said barrier layers, thereby providing a band gap in said n-type clad layer that is substantially the same as a band gap in said barrier layers by having been formed under substantially same conditions.

## 2-3. (Canceled)

- 4. (Currently amended) A group III nitride compound semiconductor light-emitting device according to claim 1, further comprising an intermediate layer which is provided so as to be in contact with a face of said n-type clad layer opposite to said light-emitting layer, said intermediate layer being devoid of aluminum.
- 5. (Currently amended) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said intermediate layer is made of comprises In<sub>x</sub>Ga<sub>1-x</sub>N, where (0

< x < 1).

- 6. (Currently amended) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said intermediate layer is made of comprises  $In_xGa_{1-x}N$ , where  $(0.01 \le x \le 0.05)$ .
- 7. (Currently amended) The group III nitride compound semiconductor light-emitting device of claim 1, wherein said n-type clad layer and said barrier layers are formed of comprise GaN.
- 8. (Previously presented) The semiconductor light-emitting device of claim 1, wherein a thickness of said well layer is approximately 30 Å and a thickness of said barrier layer is approximately 70 Å.
- 9. (Previously presented) The semiconductor light-emitting device of claim 1, further comprising:
- a cap layer formed on said light-emitting layer, said cap layer being formed of a material substantially the same as said barrier layers, and
  - a p-type clad layer formed on and contacting said cap layer.
- 10. (Previously presented) The semiconductor light-emitting device of claim 9, wherein a thickness of said p-type clad layer is in a range of approximately 180 Å to 500 Å, and a light emitted comprises green light in a wavelength range of approximately 510 nm to 530 nm.

- 11. (Previously presented) The semiconductor light-emitting device of claim 10, wherein said thickness of said p-type clad layer is in a range of approximately 240 Å to 360 Å.
- 12. (Previously presented) The semiconductor light-emitting device of claim 9, wherein a thickness of said p-type clad layer is in a range of approximately 90 Å to 390 Å, and a light emitted comprises blue light in a wavelength range of approximately 460 nm to 475 nm.
- 13. (Previously presented) The semiconductor light-emitting device of claim 12, wherein said thickness of said p-type clad layer is in a range of approximately 120 Å to 300 Å.
- 14. (Previously presented) The semiconductor light-emitting device of claim 9, wherein said p-type clad layer comprises p-type doped Al<sub>x</sub>Ga<sub>1-x</sub>N, where x ranges from approximately 0.10 to 0.14.
- 15. (Currently amended) A group III nitride compound semiconductor light-emitting device, comprising:
- a light-emitting layer of a multilayer quantum well structure comprising alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer,

wherein said n-type clad layer is made thicker than each of said barrier layers, said n-type clad layer is formed of a material substantially the same as said barrier layers, said material thereby providing a band gap in said n-type clad layer that is substantially the same as a band gap in said barrier layers by having been formed under substantially same conditions.

- 16. (Previously presented) The group III nitride compound semiconductor light-emitting device of claim 15, wherein said barrier layers comprise GaN.
- 17. (Previously presented) The group III nitride compound semiconductor light-emitting device of claim 15, further comprising:

a cap layer in contact with said light-emitting layer on a side of said light-emitting layer opposite to that contacting said n-type clad layer, said cap layer being formed of a material substantially the same as said barrier layers.

- 18. (New) A group III nitride compound semiconductor light-emitting device (LED) having enhanced color purity, comprising:
- a light-emitting layer of a multilayer quantum well structure comprising alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer on a first surface;

a cap layer being in contact with said light-emitting layer on a second surface opposite said first surface,

wherein said n-type clad layer, said cap layer and each of said barrier layers are formed of a material substantially the same, by being formed under substantially the same conditions, said substantially same material thereby providing a substantially same strain on said multilayer quantum well structure that provides an enhanced color purity of light emitted from said light emitting layer.

- 19. (New) The LED of claim 18, wherein said substantially same material comprises GaN.
- 20. (New) The LED of claim 17, further comprising:

a p-clad layer on said cap layer, said p-clad layer having a thickness selected from a range of thickness that optimizes an intensity of said color.

- 21. (New) The LED of claim 20, wherein said color comprises a green light in a main wavelength range of approximately 510 nm to 530 nm and said range of thickness of said p-clad layer is approximately 180 Å to 500 Å.
- 22. (New) The LED of claim 21, wherein said range of thickness is approximately 240 Å to 360 Å.
- 23. (New) The LED of claim 20, wherein said color comprises a blue light in a main wavelength range of approximately 460 nm to 475 nm and said range of thickness of said p-clad layer is approximately 90 Å to 390 Å.
- 24. (New) The LED of claim 23, wherein said range of thickness is approximately 120 Å to 300 Å.
- 25. (New) The LED of claim 20, wherein said p-type clad layer comprises a p-type doped  $Al_xGa_{1,x}N$ , wherein  $0.10 \le x \le 0.14$ .

- 26. (New) The LED of claim 18, said n-type clad layer is made thicker than each of said barrier layers and a thickness of said n-type clad layer is in a range of 100 Å to 500 Å.
- 27. (New) The LED of claim 19, further comprising an intermediate layer which is provided so as to be in contact with a face of said n-type clad layer opposite to said light-emitting layer, said intermediate layer being devoid of aluminum.
- 28. (New) The LED of claim 27, wherein said intermediate layer comprises  $In_xGa_{1-x}N$ , where  $(0 \le x \le 1)$ .
- 29. (New) The LED of claim 27, wherein  $0.01 \le x \le 0.05$ .
- 30. (New) A group III nitride compound semiconductor light-emitting device according to claim 5, wherein said intermediate layer comprises a material devoid of aluminum.
- 31. (New) A group III nitride compound semiconductor light-emitting device according to claim 7, further comprising an intermediate layer which is provided so as to be in contact with a face of said n-type clad layer opposite to said light-emitting layer, said intermediate layer comprising a material devoid of aluminum.